

FIG.1A

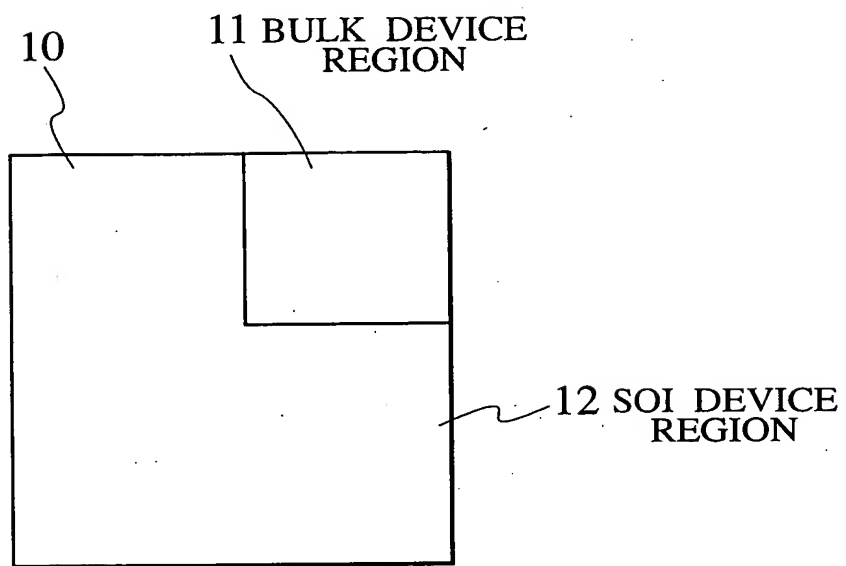


FIG.1B

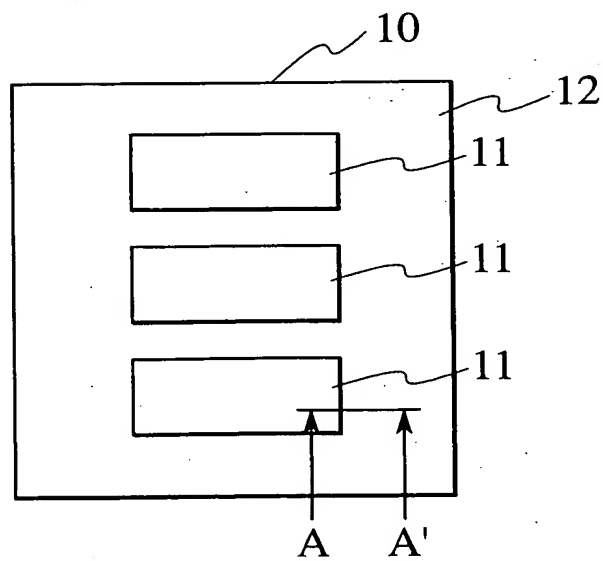


FIG. 2

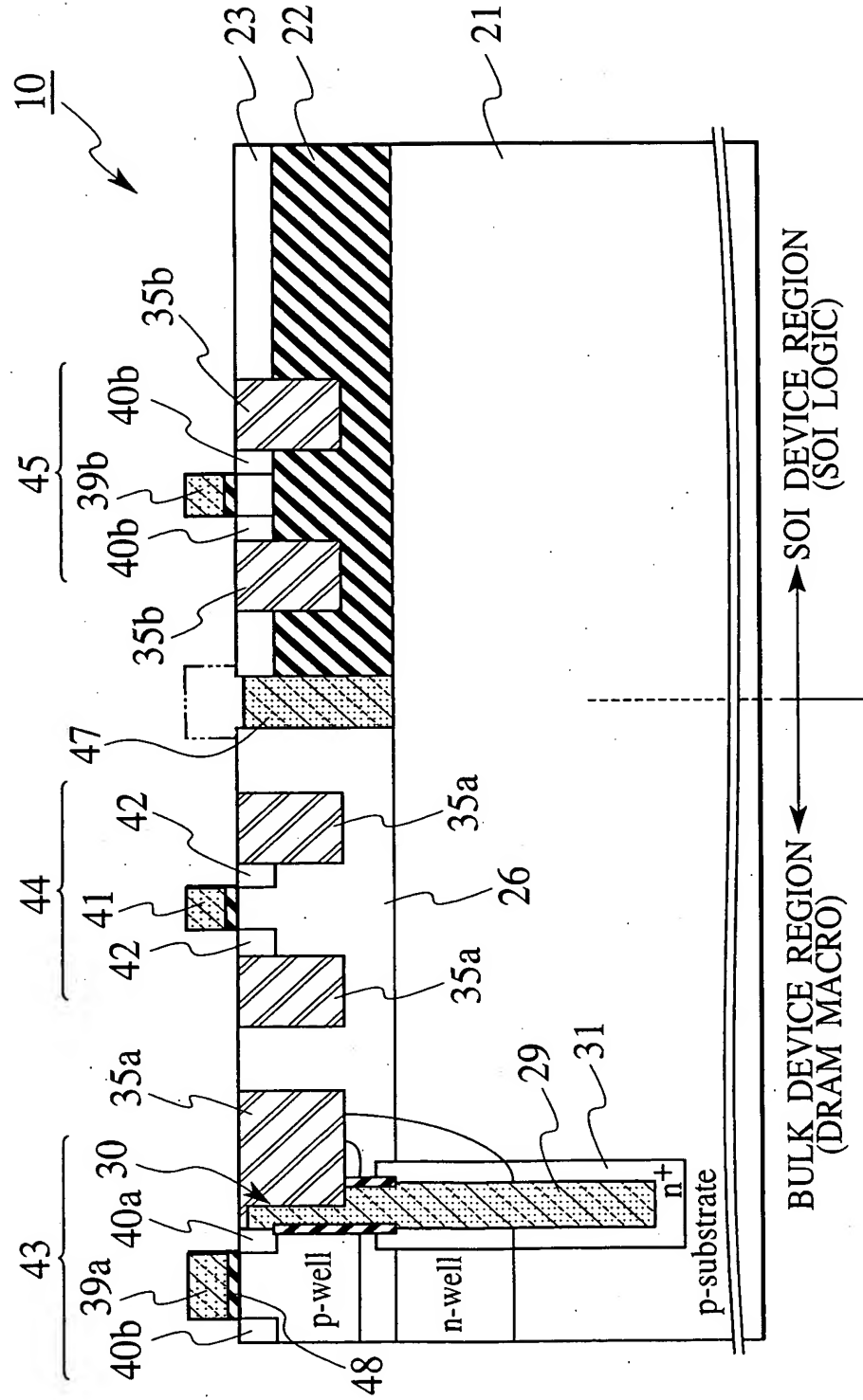


FIG.3A

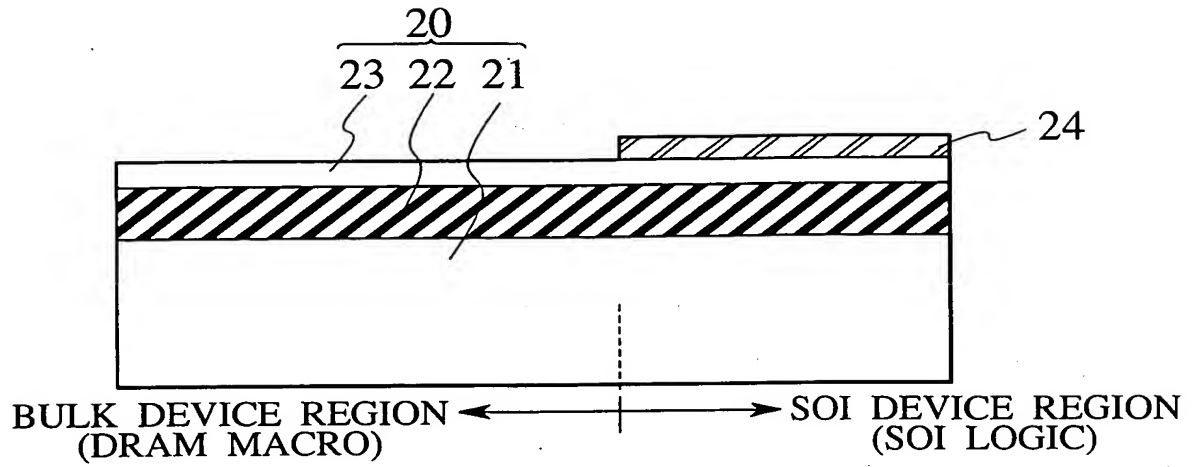


FIG.3B

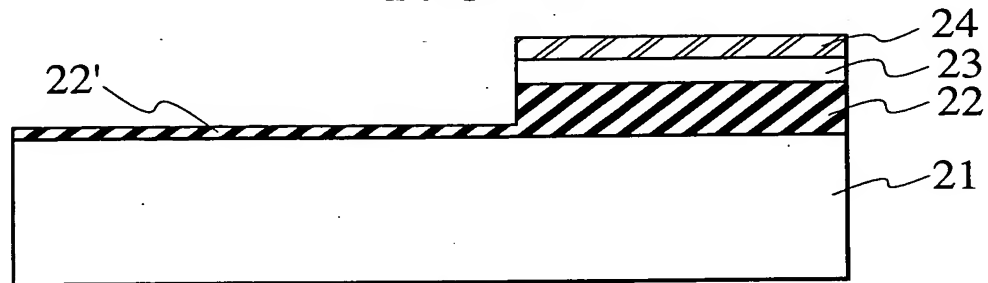


FIG.3C

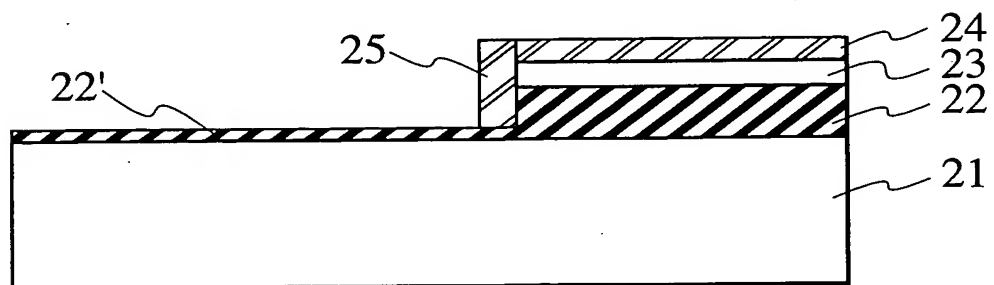


FIG.3D

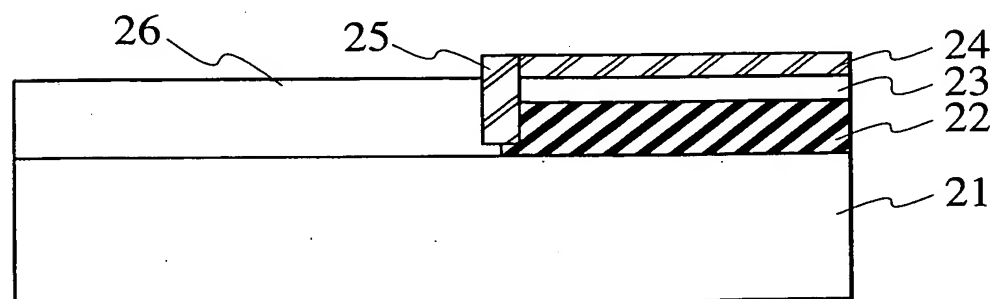


FIG.3E

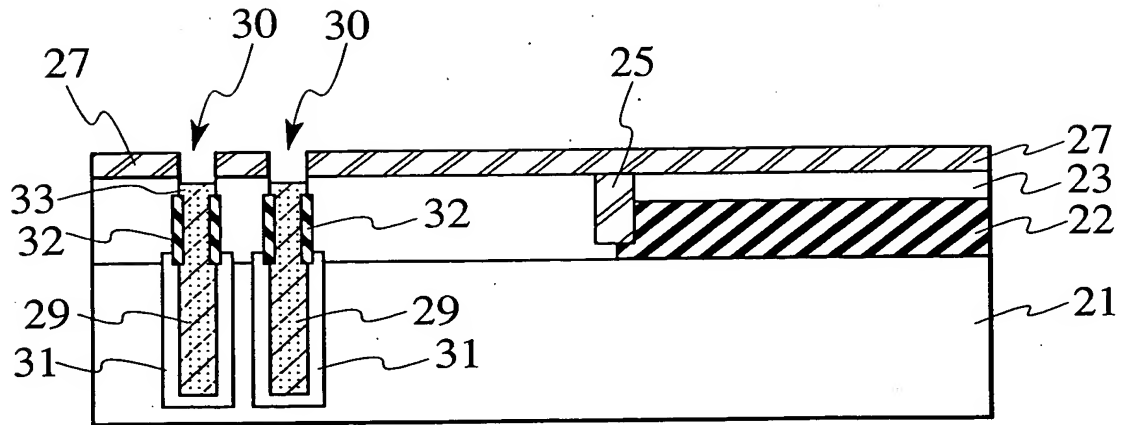


FIG.3F

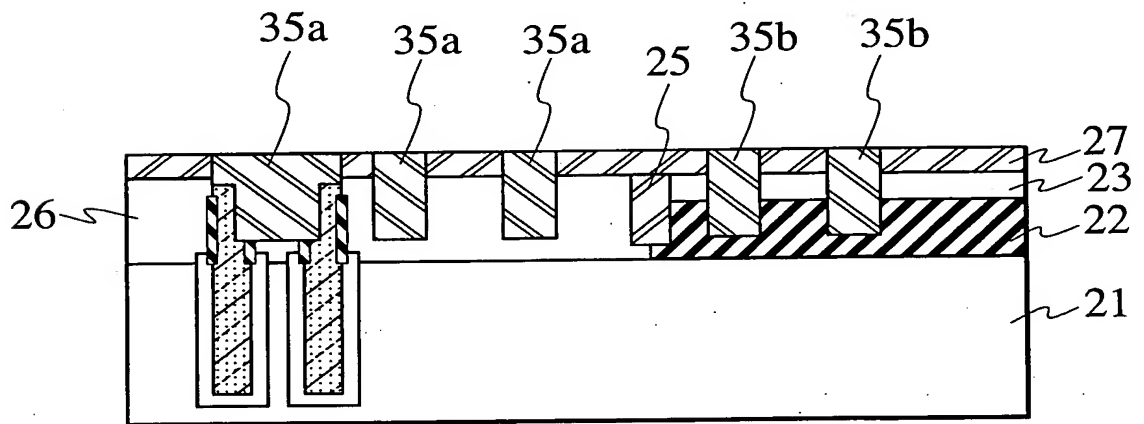
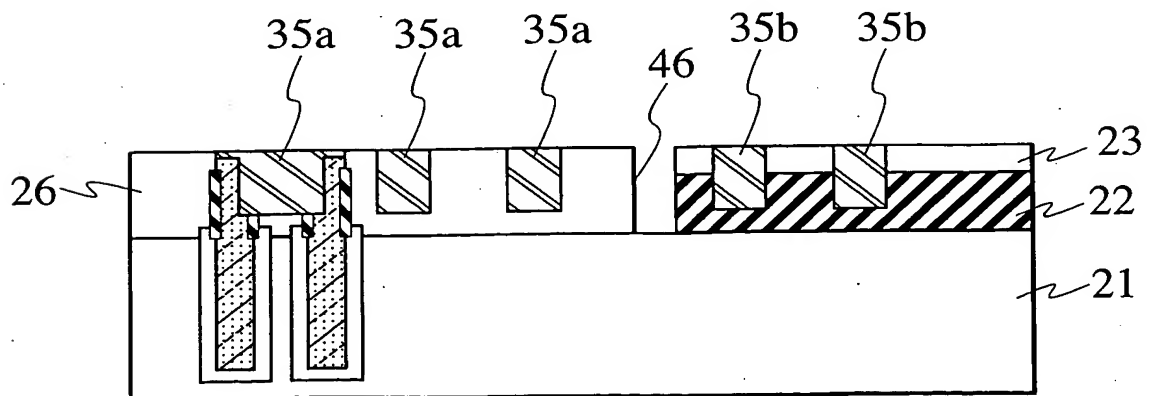


FIG.3G



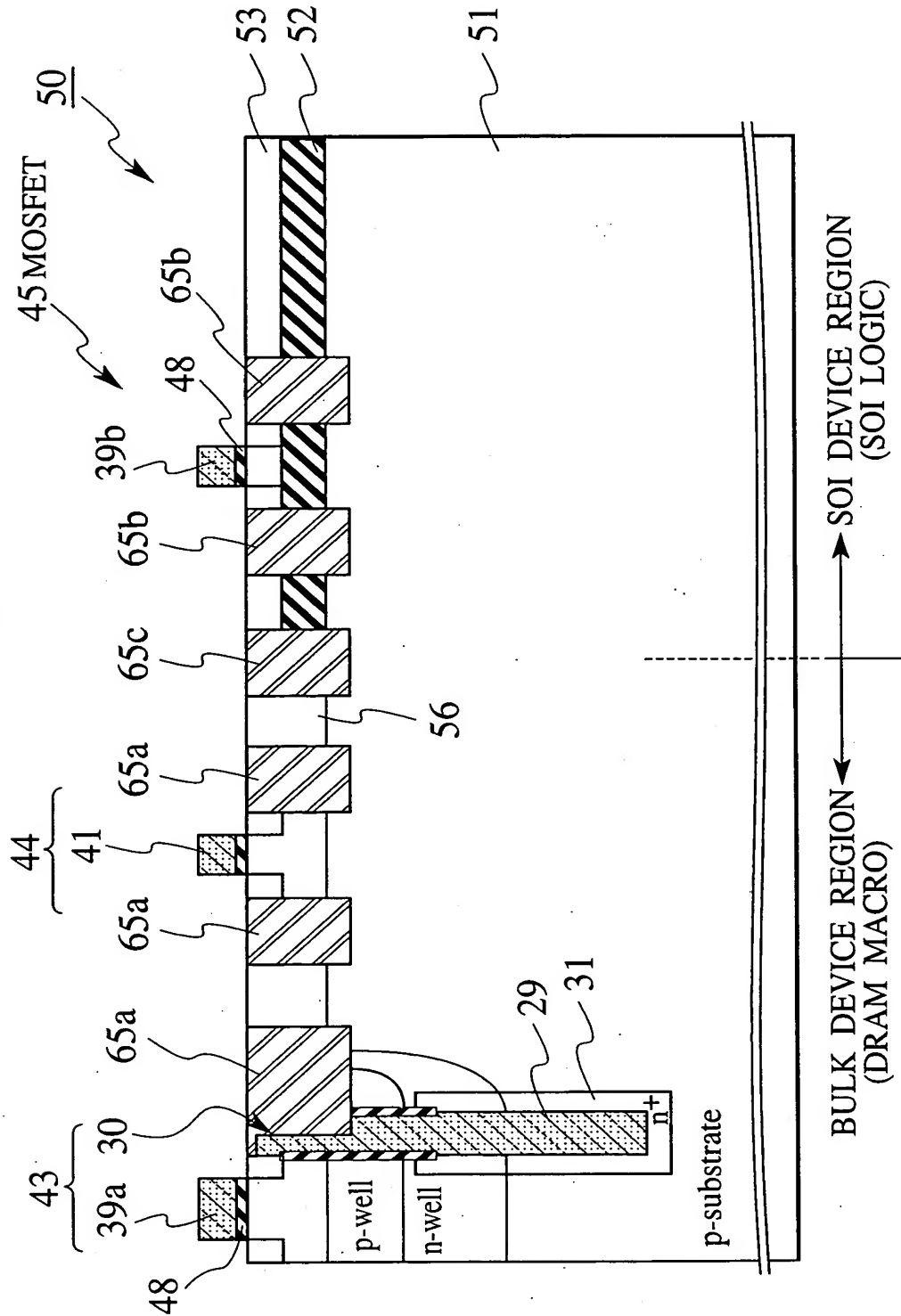


FIG.5A

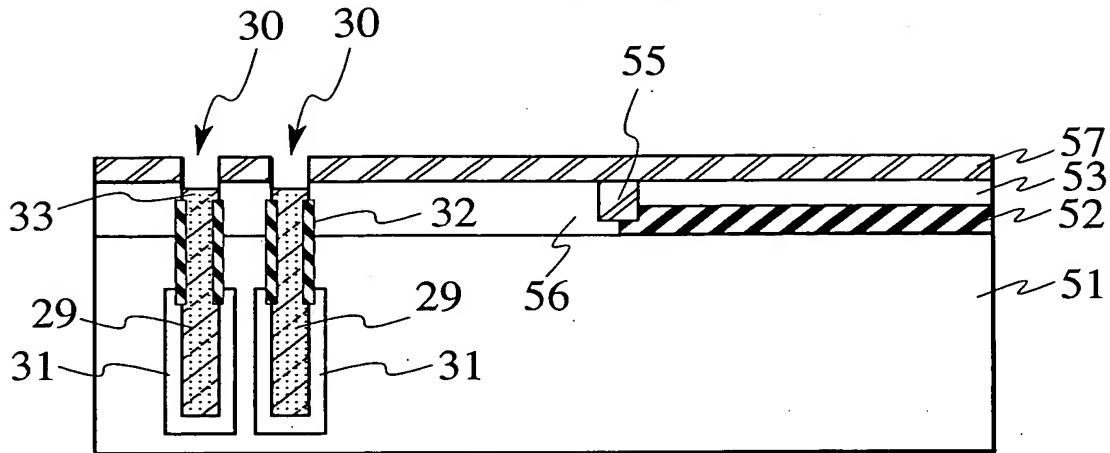


FIG.5B

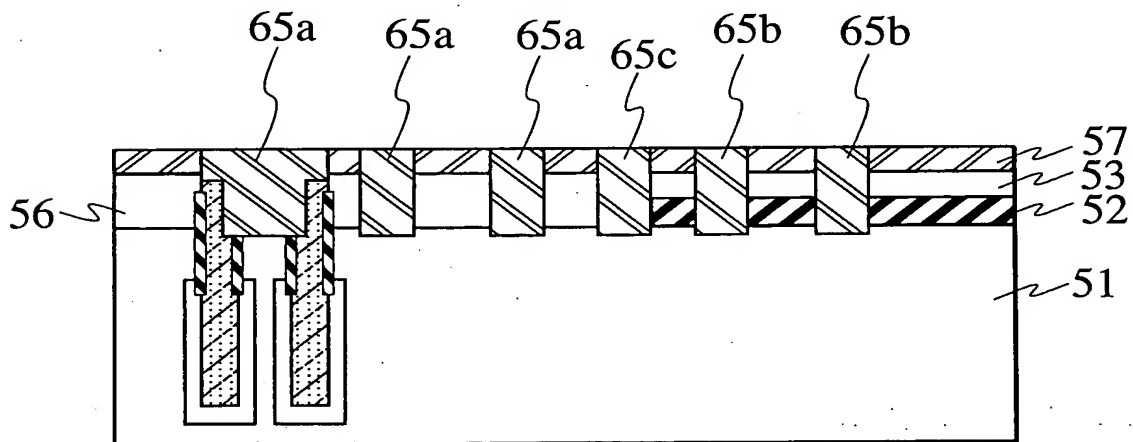


FIG.5C

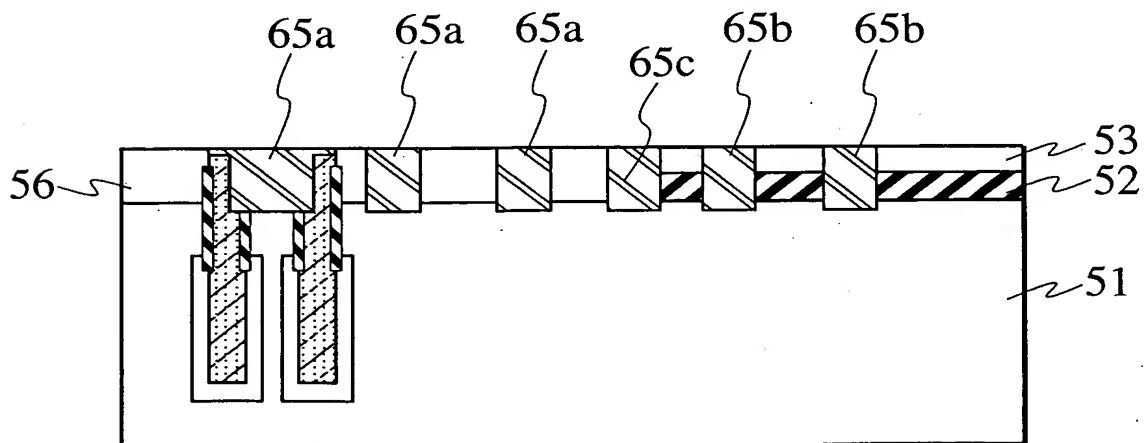


FIG.6

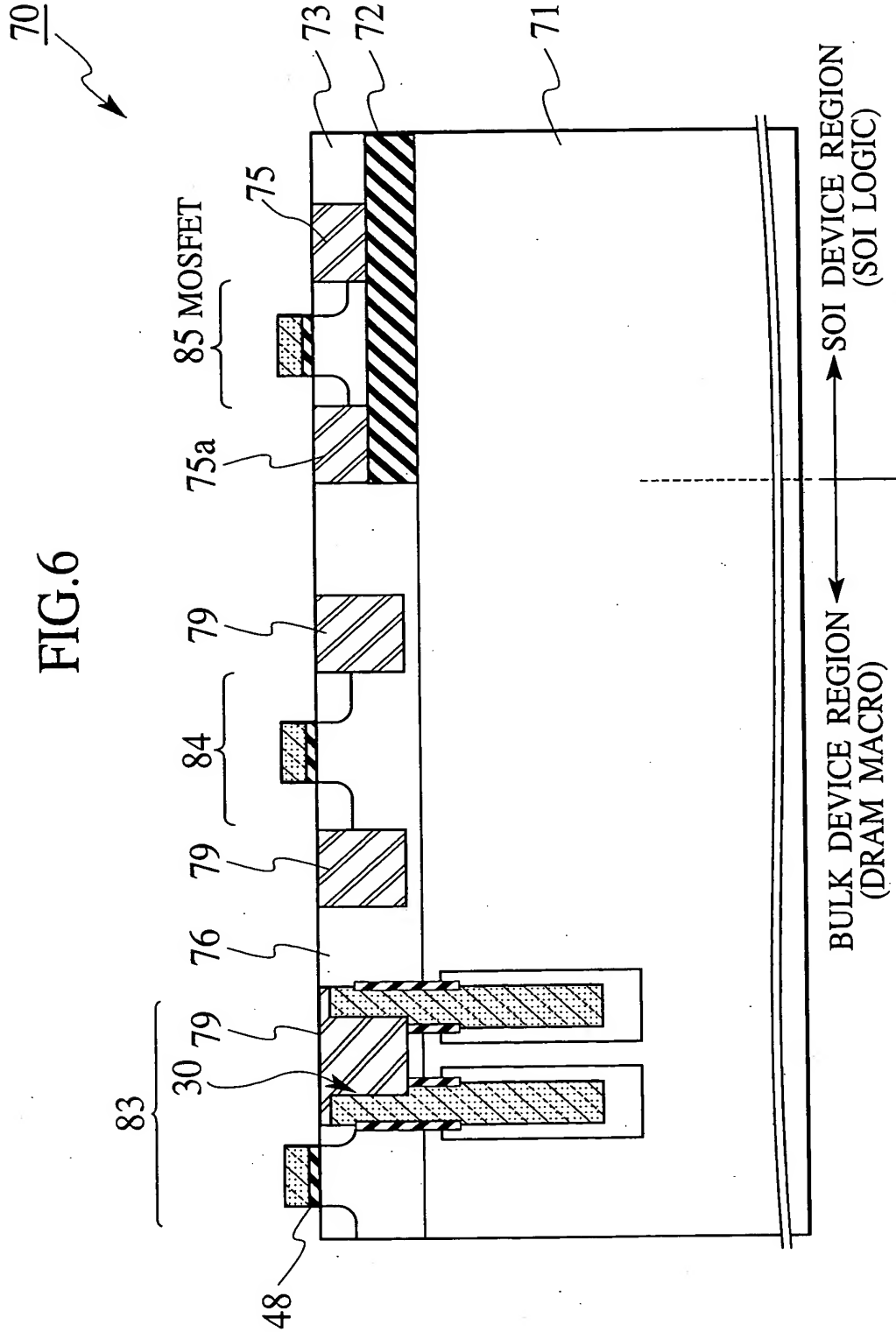


FIG.7A

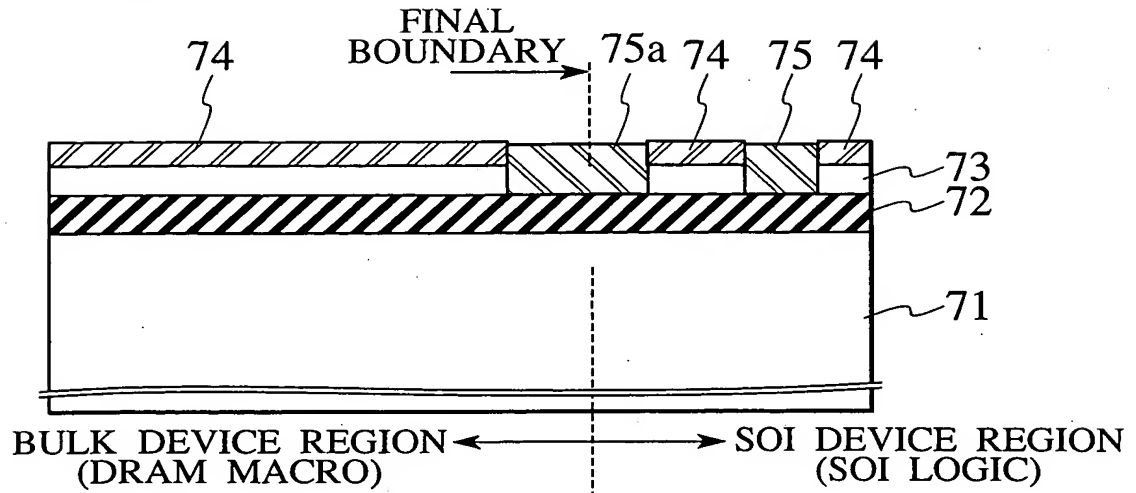


FIG.7B

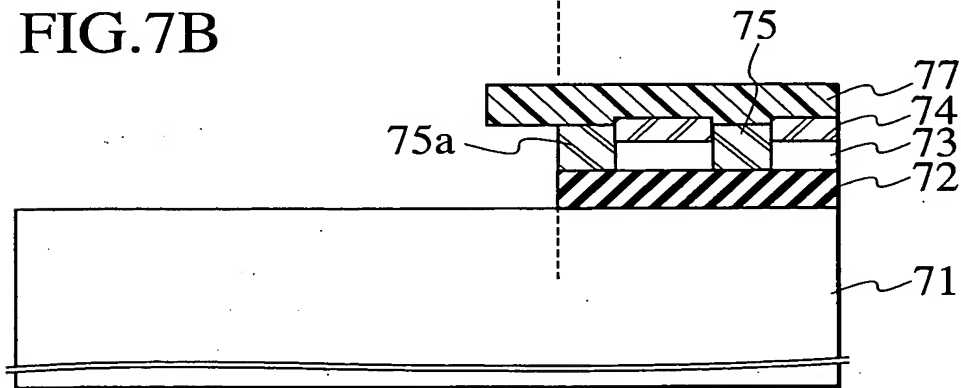


FIG.7C

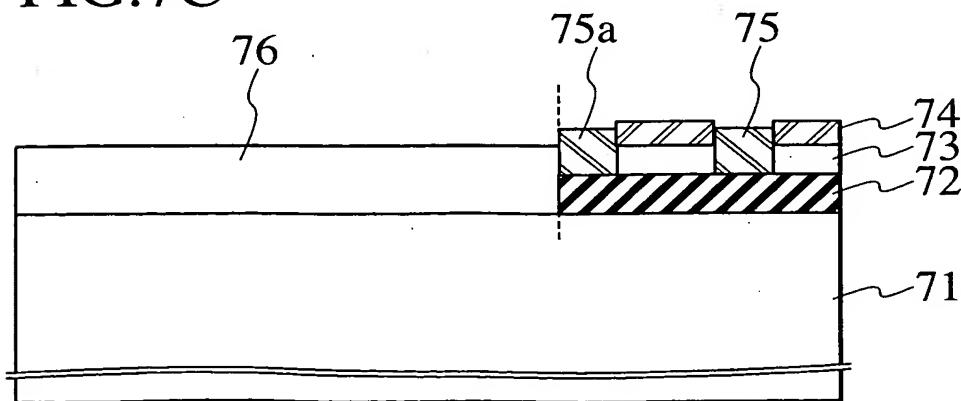




FIG. 7D

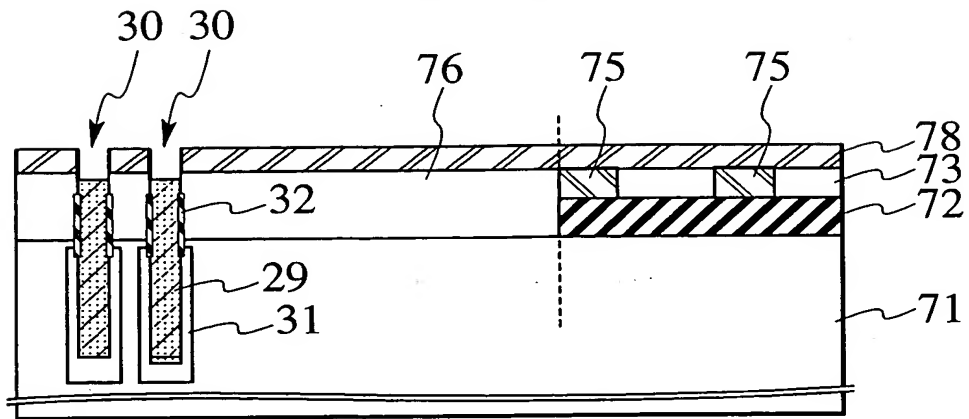


FIG. 7E

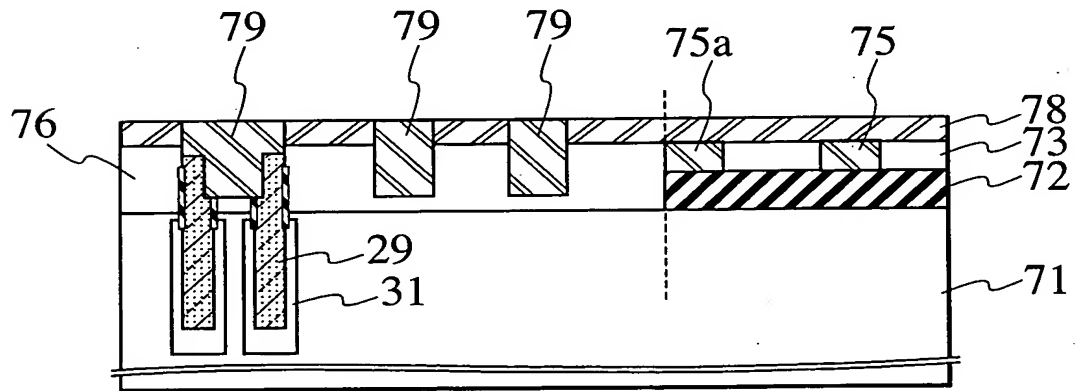


FIG. 7F

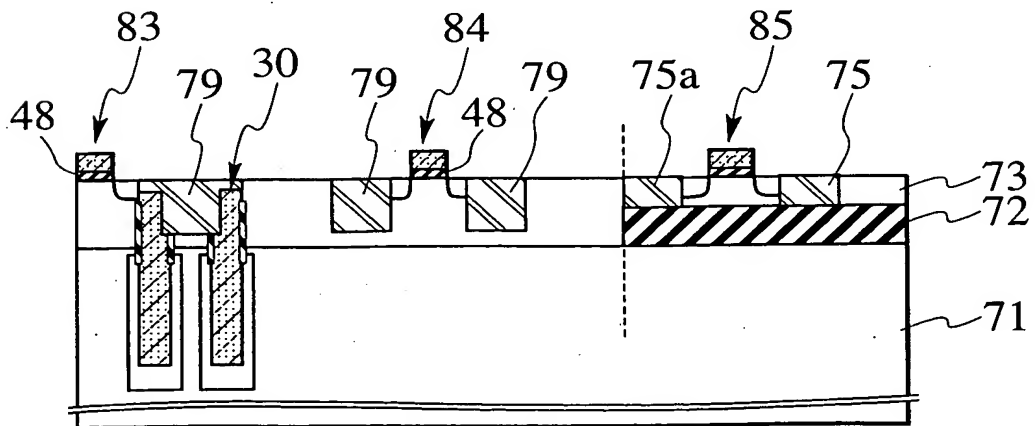


FIG.8A

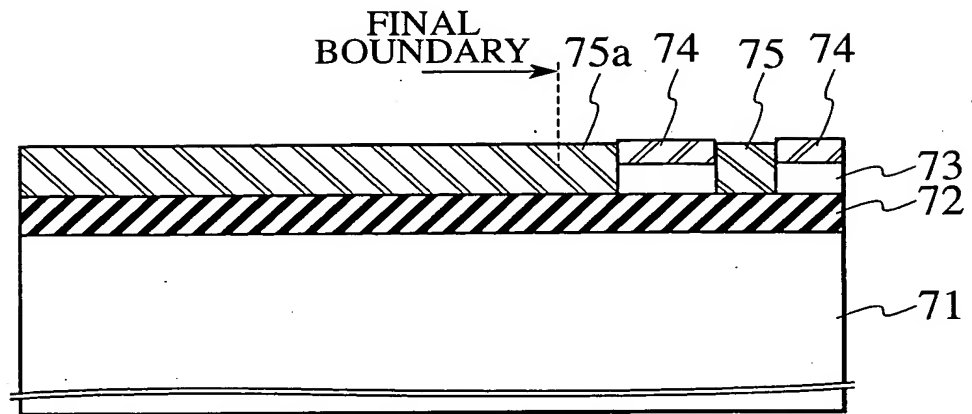


FIG.8B

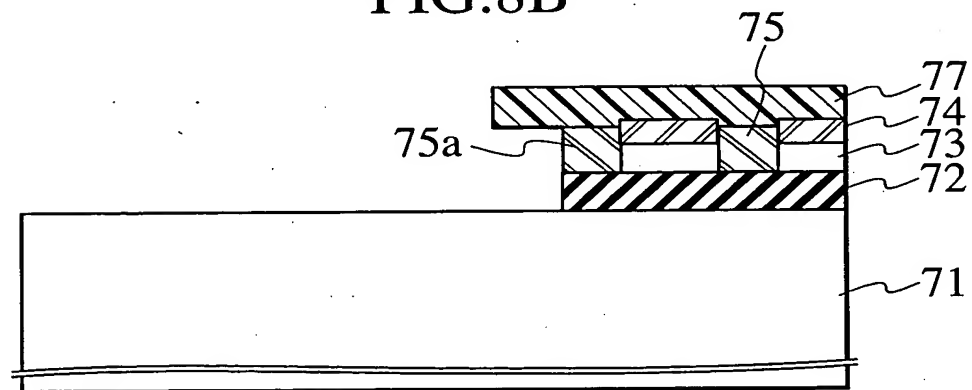


FIG.8C

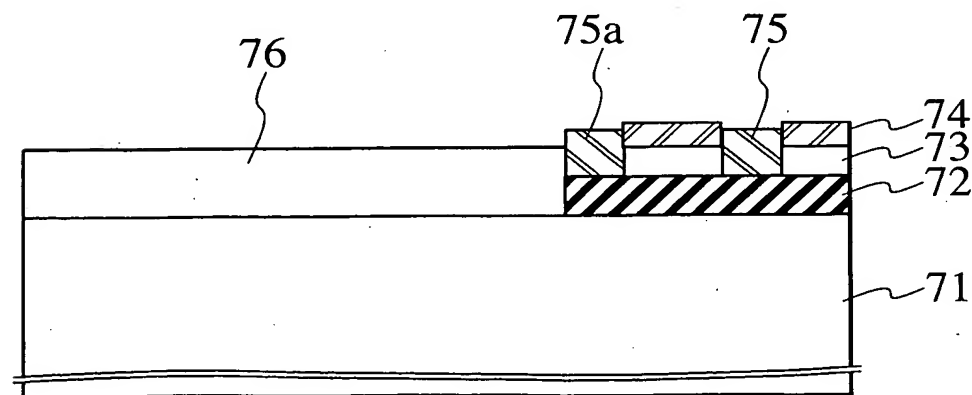
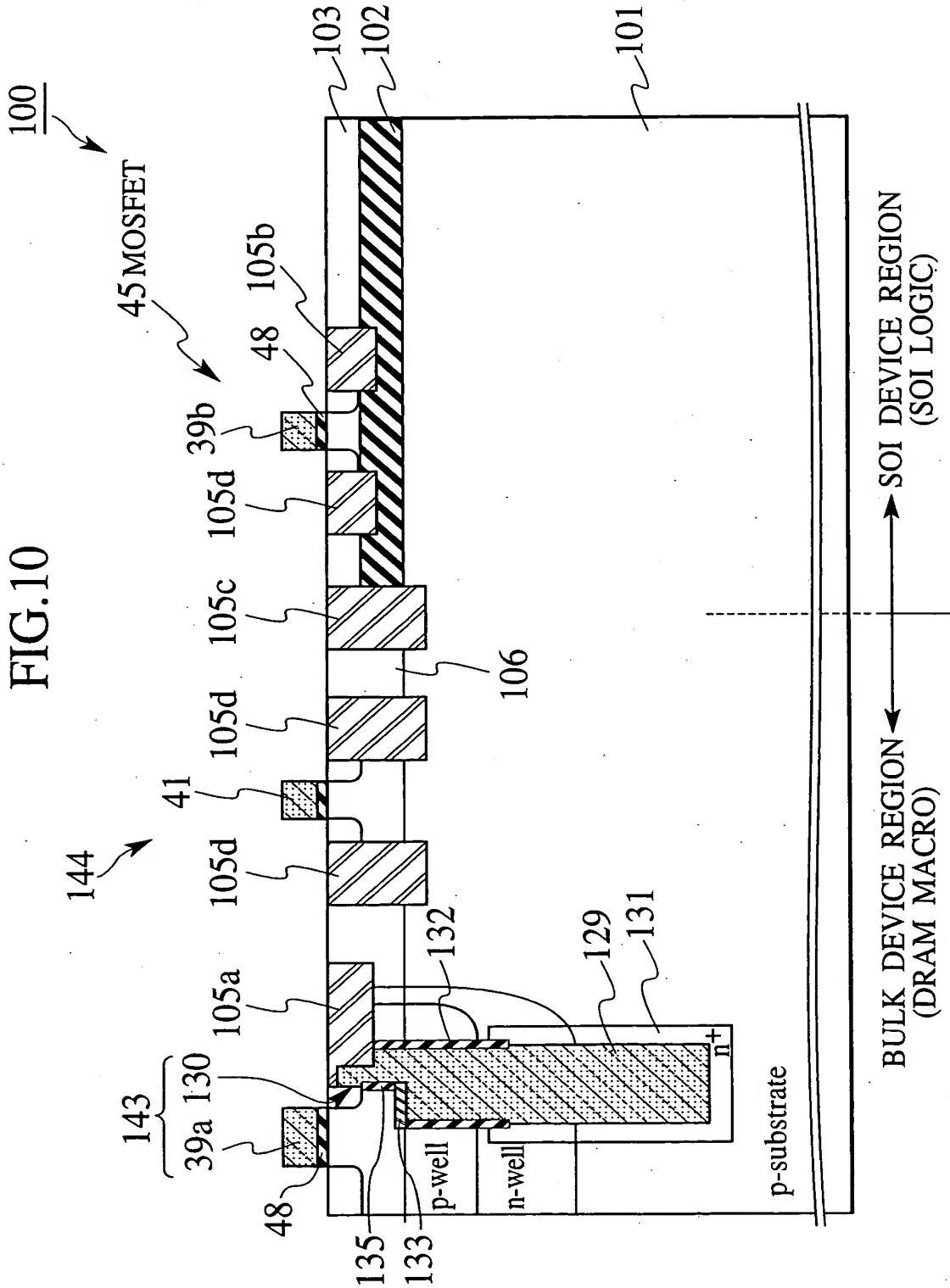
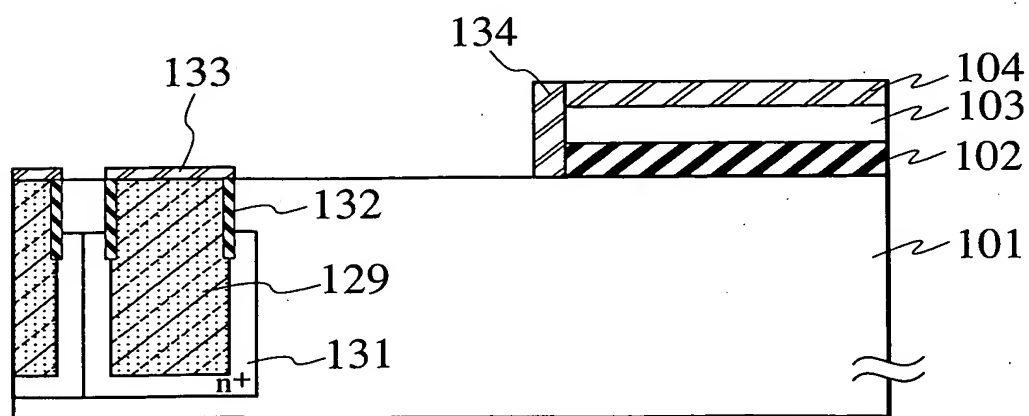
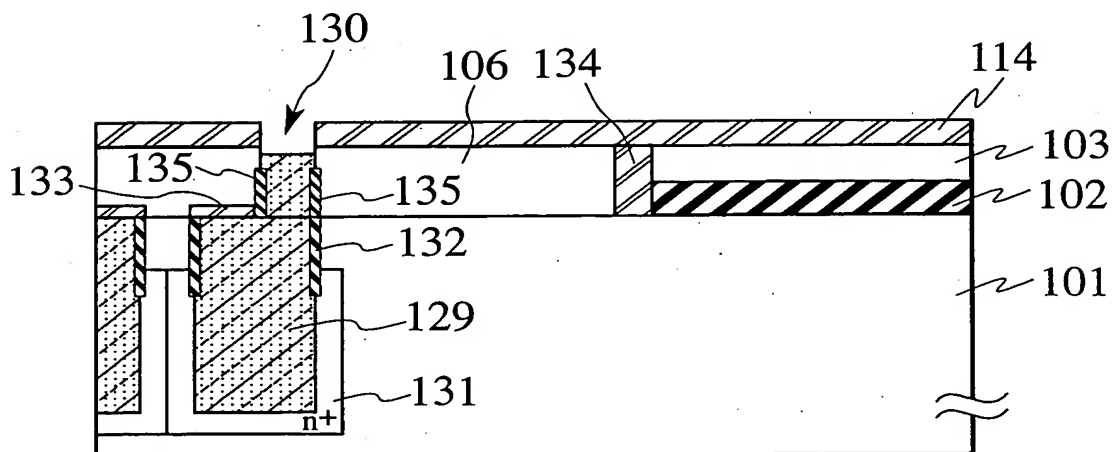


FIG. 9B is a cross-sectional view of a semiconductor device. The device is divided into two main regions by a vertical dashed line: the BULK DEVICE REGION (DRAM MACRO) on the left and the SOI DEVICE REGION (SOI LOGIC) on the right. The BULK REGION features a p-substrate with a p-well, n-well, and n+ region. The SOI REGION features a MOSFET structure with labels 90B, 45, 93, 92, 91, 96, 97a, 97b, 97c, 97d, 41, 39a, 39b, 48, 30, 29, and 31. A dashed line separates the two regions.







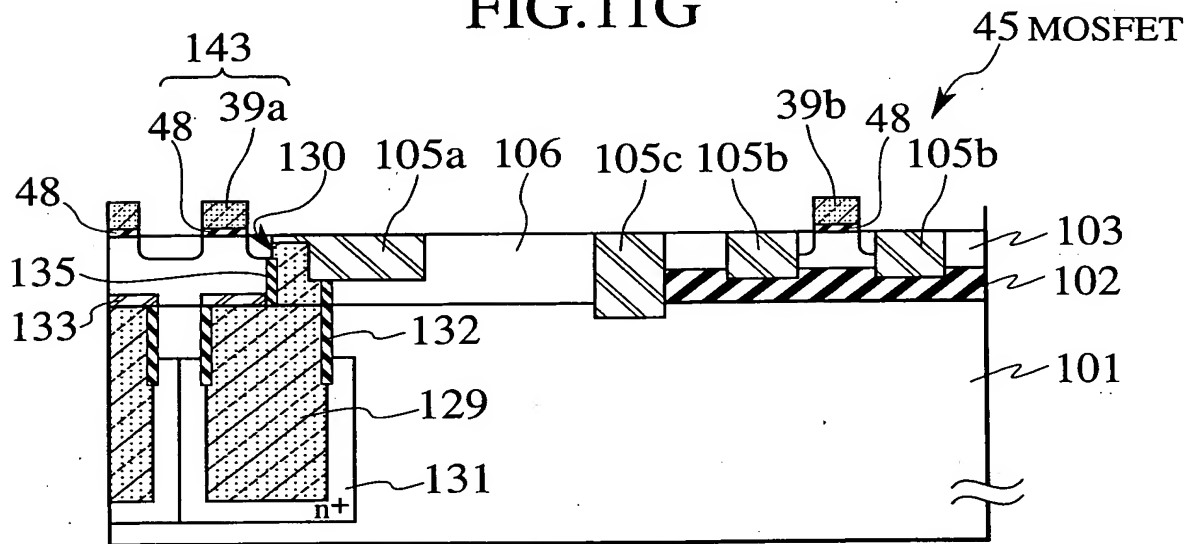


FIG.12

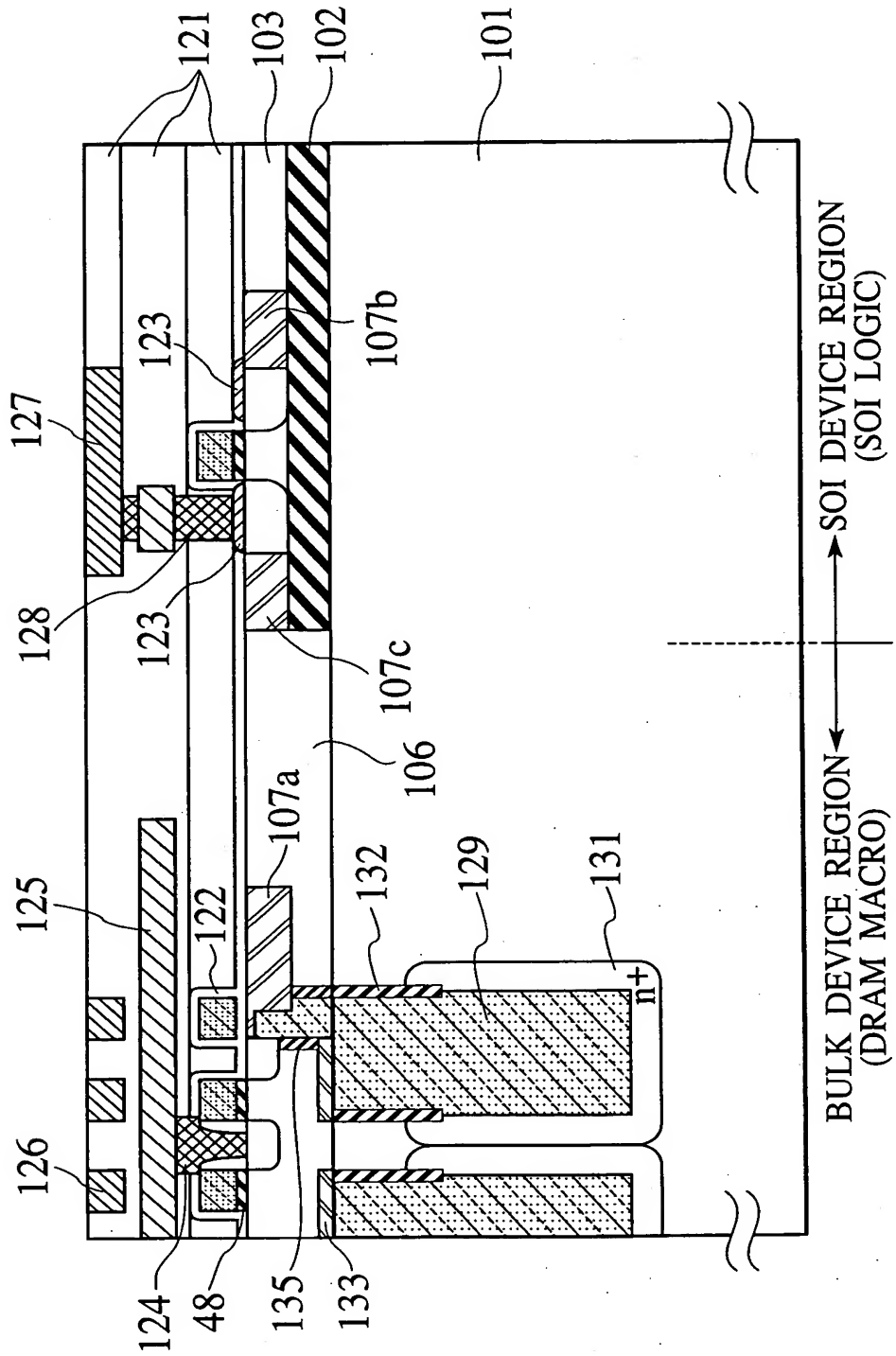




FIG.13

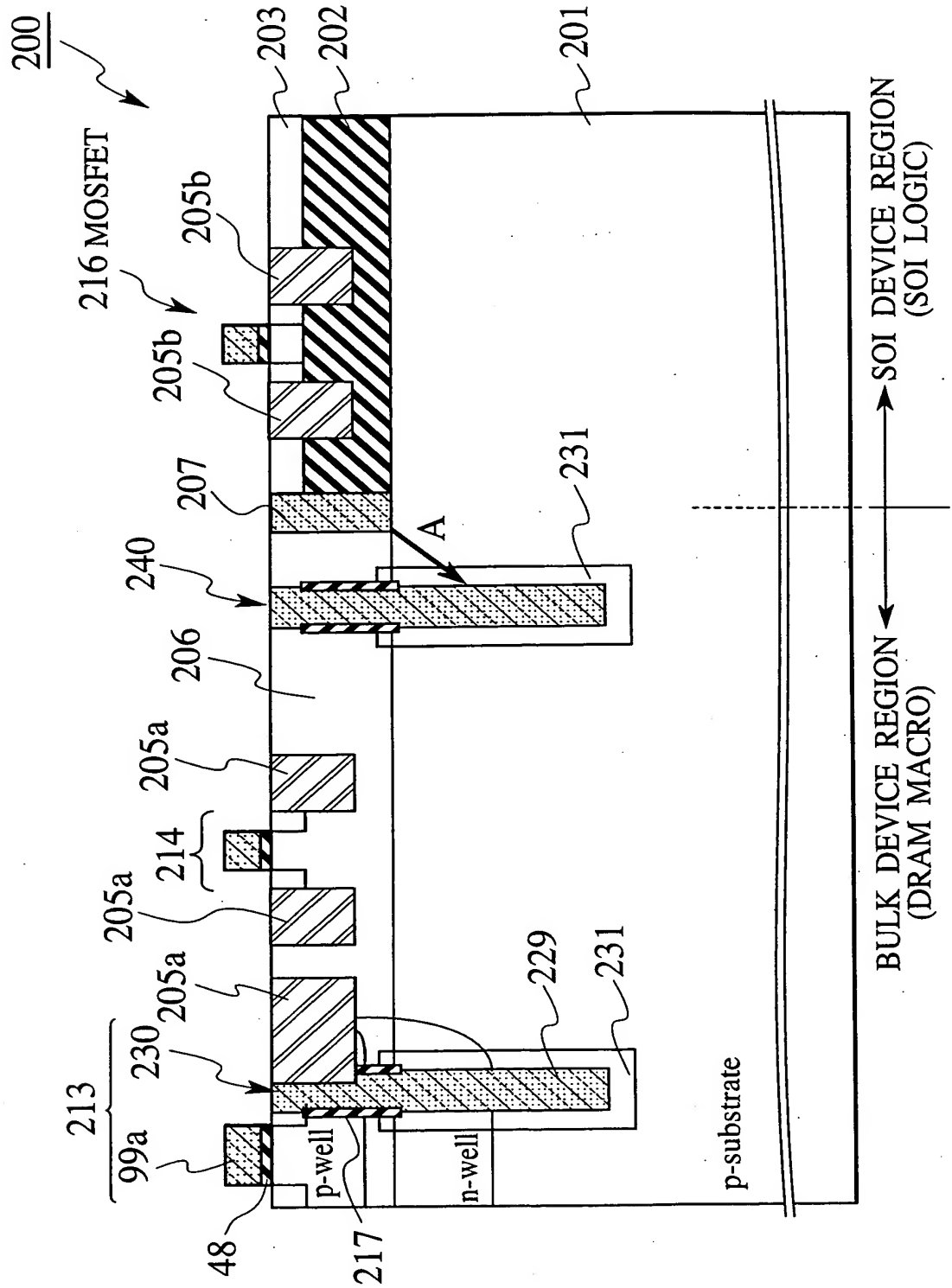


FIG. 14

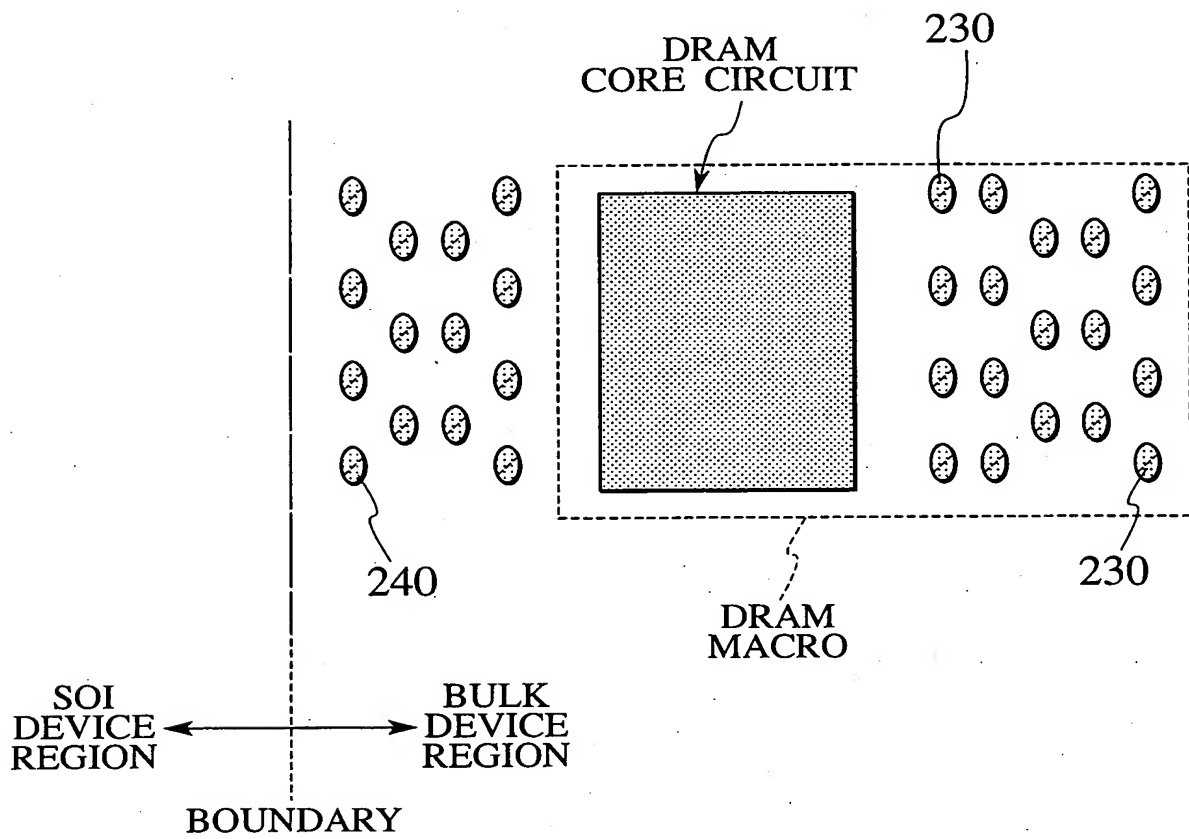


FIG.15A

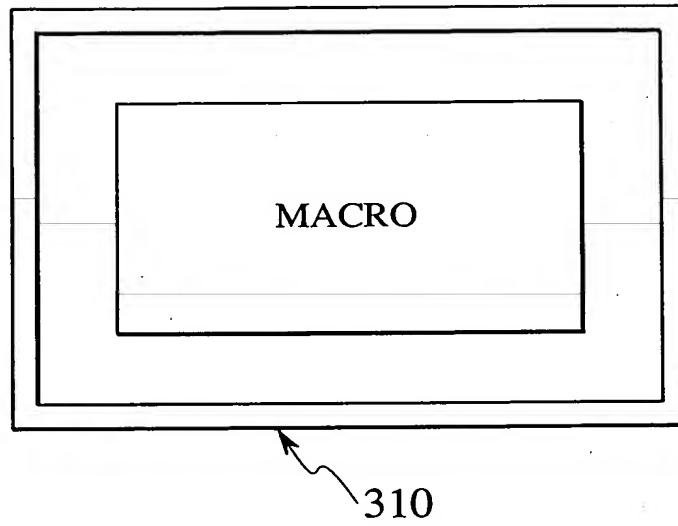


FIG.15B

